

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>F03-354-USDiv</b>		Application Number <b>10/634,836</b>		
				Applicant(s) <b>Hisaki KATO, et al.</b>				
				Filing Date <b>August 6, 2003</b>		Group Art Unit <b>2822-1656</b>		
<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<b>FOREIGN PATENT DOCUMENTS</b>								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
CMK		H7-7182	01/10/99	Japan	<del>          </del>		AGS	
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
CMK		Japanese Office Action, dated May 24, 2005, with partial English translation						
CMK		NAKAMURA, et al., "Ridge-geometry InGaN multi-quantum-well-structure laser diodes", APPLIED PHYSICS LETTERS, September 2, 1996, Vol. 69, No. 10, pp. 1477-1479						
EXAMINER				DATE CONSIDERED				
				11/10/05				
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